

M617x Series Stratum 3 3.2 x 5.0 mm, 3.0, 3.3 & 5.0 V, HCMOS or Clipped Sine Wave Precision TCXO/TCVCXO

Product Features

- Stratum 3 performance with holdover stability (0.30 ppm) over industrial temperature range (-40 °C to +85 °C)
- 3.0 V, 3.3 V and 5.0 V versions
- · Low phase noise and great g-sensitivity performance
- · Tristate Function standard



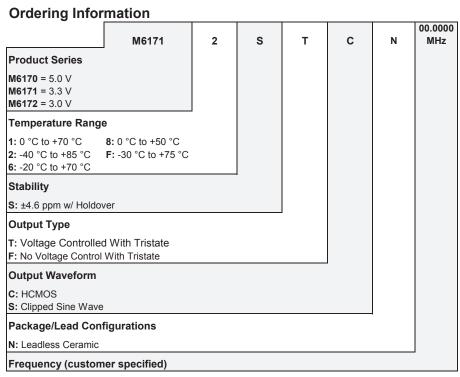


Product Description

MtronPTI's M617x Series TCXO's and TCVCXO's provide design engineers with low voltage, surface mount products with extremely tight stability over temperature and time. MtronPTI's unique approach to crystal compensation enables these devices to achieve full Stratum 3 temperature stability including holdover from -40 °C to +85 °C. Specially processed crystals enable the M617x to achieve consistent long-term stability and minimal frequency shift after reflow. This processing also achieves excellent g-sensitivity (1.2 ppb/g). The low phase noise (-156 dBc/Hz at 100 kHz) makes the M617x ideal for the design engineer working on high data-rate, low BER data communication network products.

Product Applications

The M617x Series is ideally suited for a wide range of applications such as SONET, SDH, SERDES, GSM, CDMA, 3G, 4G, Gig-Ethernet, 10G and 40G systems. Standard output for the M617x series is either HCMOS compatible or clipped sine wave. Additionally the M617x draws as little as 1.5 mA with a 3.3 volt supply at 13 MHz. This low power consumption provides a distinct advantage over similarly specified ovenized oscillators for power-sensitive remote applications. The M617x series offers ±9.2 ppm minimum pull range with excellent tuning linearity performance for critical PLL applications. This series is available in selective frequencies from 8 MHz to 52 MHz.



M6170Sxxx, M6171Sxxx & M6172Sxxx - Custom datasheets.



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Performance Characteristics

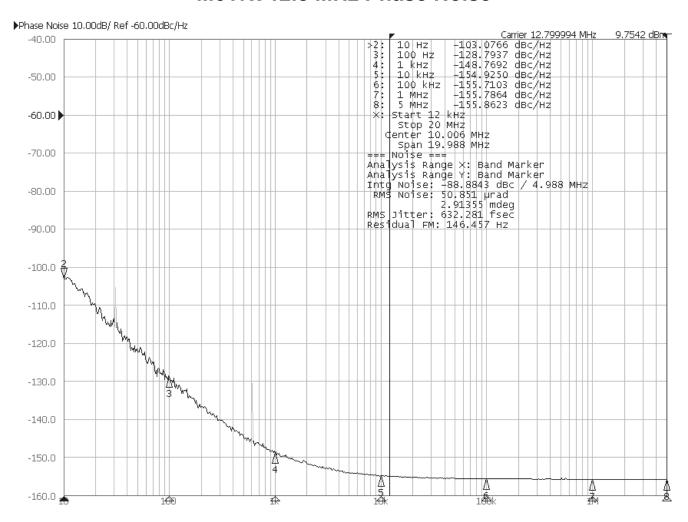
	Parameter	Symbol				Units	Conditions/Notes				
	Frequency Range	F_R	8		52	MHz					
	Operating Temperature	T _A	(See Ordering Information)			°C					
	Storage Temperature	T _{STG}	-55		+125	°C					
	Frequency Tolerance @ +25 °C	ΔF/F	-1.0		+1.0	ppm	For TCXO only				
	Frequency Stability	ΔF _T /F	-0.30		+0.30	ppm	Stability vs. Temperature (F _{MIN} -F _{MAX})/2				
			-4.6		+4.6	ppm	Overall stability for 10 years				
			-0.34		+0.34	ppm	Holdover stability for 24 hrs over operating temperature				
	Stability vs. Reflow		-1.0		+1.0	ppm	·				
	Frequency vs. Supply	ΔF _{VDD} /F		±0.02	±0.1	ppm	For ±5% supply voltage variation				
	Frequency vs. Load	ΔF _{LOAD} /F		±0.02	±0.1	ppm	For ±5% load variation				
	Aging (First Year)		-1.0		+1.0	ppm	F ₀ ≤ 20 MHz				
	Aging (First Year)		-2.0		+2.0	ppm	F ₀ > 20 MHz				
	Aging (10 Year)		-3.0		+3.0	ppm	F ₀ ≤ 20 MHz (includes first year)				
	Aging (10 Year)		-5.0		+5.0	ppm	F ₀ > 20 MHz (includes first year				
	Supply Voltage	V_{DD}	(See C	rdering Infor	mation)	V	±5% voltage tolerance				
	Supply Current	I _{DD}	2.0		3.0	mA	HCMOS output at 13 MHz				
	(Reference to V _{DD} = 3.3 V)		3.0		4.0	mA	HCMOS output at 26 MHz				
	,		5.5		6.5	mA	HCMOS output at 52 MHz				
Suc			1.3		1.9	mA	Clipped Sine Wave output at 13 MHz				
atic			1.7		2.3	mA	Clipped Sine Wave output at 26 MHz				
Electrical Specifications			2.8		3.5	mA	Clipped Sine Wave output at 52 MHz				
၁ဓင	Output Logic Levels	V _{OL}			20	% V _{DD}	$I_{OH}/I_{OL} = \pm 4 \text{ mA}, V_{DD} = +3.0 \text{ V}$				
Š	(HCMOS)	V _{OH}	80		20	% V _{DD}	$I_{OH}/I_{OL} = \pm 4 \text{ mA}, V_{DD} = +3.0 \text{ V}$				
<u>S</u>	Output Level	V _{OUT}	1.0			V _{pk-pk}	$F_0 \le 40 \text{ MHz}$				
t	(Clipped Sine Wave)	V _{OUT}	0.8			V _{pk-pk}	$F_0 > 40 \text{ MHz}$				
E	Symmetry (Duty Cycle)	t _{DC}	40	50	60	%	Ref. to ½ V _{DD} HCMOS Only				
	Rise/Fall Time	t _R /t _F	10		6.5	ns	Ref. 10% to 90% HCMOS only				
	Output Load	R' F		15 pF	0.0	110	HCMOS Output				
	Output Loud			10 kΩ 10 p	F		Clipped Sine Wave Output				
	Frequency Adjustment		-10		+10	ppm	Over Control Voltage Range				
	Control Voltage Range		0.3	1.50	2.7	V	For V _{DD} = 3.0 V				
			0.3	1.65	3.0	V	For V _{DD} = 3.3 V				
			0.5	2.50	4.5	V	For V _{DD} = 5.0 V				
	Input Leakage Current		-50		+50	μA					
	Input Resistance		100			kΩ					
	Linearity				5	%					
	Modulation Bandwidth		2 kHz								
	Tristate Function		70			% V _{DD}	Output enabled. Logic "1" or "Open"				
					30	% V _{DD}	Output disabled. Logic "0" or "GND"				
	Tristate Leakage Current	1	-100		+100	μA	· · · · · · · · · · · · · · · · · · ·				
	Phase Noise	1		-102		dBc/Hz	@ 10 Hz Offset				
	(Typical 12.8 MHz HCMOS)			-129		dBc/Hz	@ 100 Hz Offset				
	· · ·			-149		dBc/Hz	@ 1 kHz Offset				
				-155		dBc/Hz	@ 10 kHz Offset				
				-156		dBc/Hz	@ 100 kHz Offset				
ē	Shock	MIL-STD-202, Method 213, Condition C (100 g)									
ent	Vibration	MIL-STD-202, Methods 201 & 204 (10 g from 10 Hz to 2000 Hz)									
Environmental	Solderability	EIAJ-STD-0	002								
nvir	Package	3.2 mm x 5.	0 mm x 1.5	8 mm, SMT	RoHS Com	pliant)					
ш	Max Soldering Conditions	See solder	profile								
	_	<u> </u>									



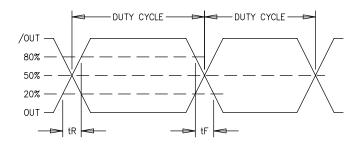
 3.2×5.0 mm, 3.0, 3.3 & 5.0 V, HCMOS or Clipped Sine Wave Precision TCXO/TCVCXO

Phase Noise Plot

M617x 12.8 MHz Phase Noise



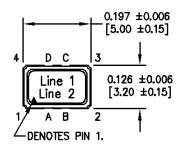
Output Waveform (HCMOS Output)

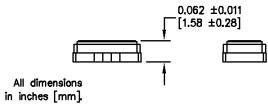


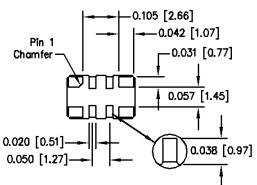


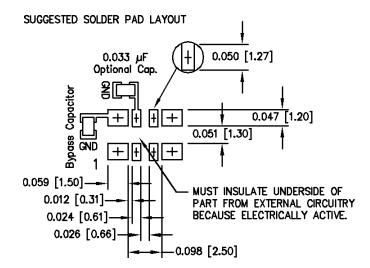
3.2 x 5.0 mm, 3.0, 3.3 & 5.0 V, HCMOS or Clipped Sine Wave **Precision TCXO/TCVCXO**

Product Dimension & Pinout Information









Pad Connections:

1= EFC or n/c

A= n/c

В= п/с

2= Ground 3= Output

C= Enable/Disable or n/c

D= Low Phase Noise capacitor or n/c

4= Supply Voltage

Marking

Line 1: M61 YM

Line 2: XXMXXXX



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Handling Information

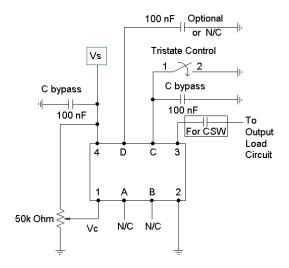
Although protection circuitry has been designed into the M617x oscillator, proper precautions should be taken to avoid exposure to electrostatic discharge (ESD) during handling and mounting. MtronPTI utilizes a human-body model (HBM) and a charged-device model (CDM) for ESD-susceptibility testing and protection design evaluation. ESD voltage thresholds are dependent on the circuit parameters used to define the mode. Although no industry-wide standard has been adopted for the CDM, a standard HBM (resistance = 1500 Ω , capacitance = 100 pF) is widely used and therefore can be used for comparison purposes. The HBM ESD threshold presented here was obtained using these circuit parameters.

Model	ESD Threshold, Minimum	Unit		
Human Body	1500*	V		
Charged Device	1500*	V		

* MIL-STD-833D, Method 3015, Class 1



Typical Test Circuits



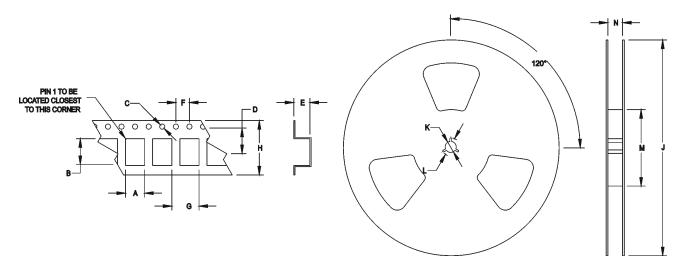
Test Circuit - N Package With Tristate



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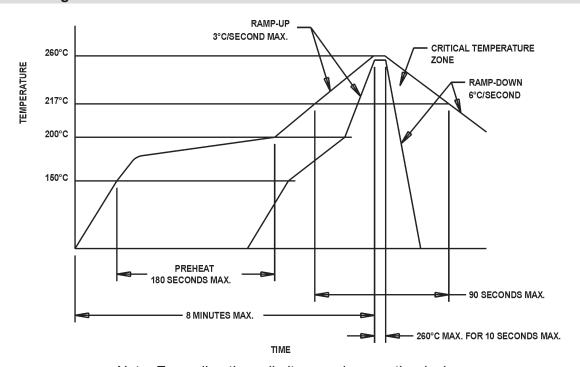
Tape & Reel Specifications

(all measurements are in mm)	Α	В	С	D	E	F	G	Н	J	K	Г	M	N
M617x	3.6	5.4	1.5	5.5	1.9	4	8	12	180	13	20.2	60	12



Standard Tape and Reel: 1000 parts per reel

Maximum Soldering Conditions



Note: Exceeding these limits may damage the device.



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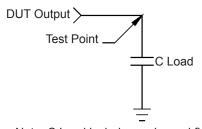
Quality Parameters

Environmental Specifications/Qualification Testing Performed							
Test	Test Method	Test Condition					
Electrical Characteristics	Internal Specification	Per Specification					
Frequency vs. Temperature	Internal Specification	Per Specification					
Mechanical Shock	MIL-STD-202, Method 213, C	100 g's					
Vibration	MIL-STD-202, Method 201-204	10 g's from 10-2000 Hz					
Thermal Cycle	MIL-STD-883, Method 1010, B	-55 Deg. C to +125 Deg. C, 15 minute Dwell, 10 cycles					
Aging	Internal Specification	168 Hours at 105 Degrees C					
Gross Leak	MIL-STD-202, Method 112	30 Second Immersion					
Fine Leak	MIL-STD-202, Method 112	Must meet 1x10-8					
Solderability	MIL-STD-883, Method 2003	8 Hour Steam Age – Must Exhibit 95% coverage					
Resistance to Solvents	MIL-STD-883, Method 2015	Three 1 minute soaks					
Physical Dimensions	MIL-STD-883, Method 2016	Per Specification					
Internal Visual	Internal Specification	Per Internal Specification					

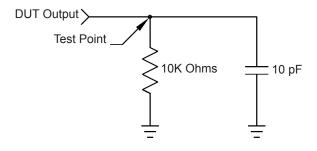
Load Circuit

Load Circuit #2 - HCMOS Output

Load Circuit #7 - Clipped Sine Wave Output



Note: C Load includes probe and fixturing.



For custom products or additional specifications contact our sales team at 800.762.8800 (toll free) or 605.665.9321

For more information on this product visit the MtronPTI website at www.mtronpti.com